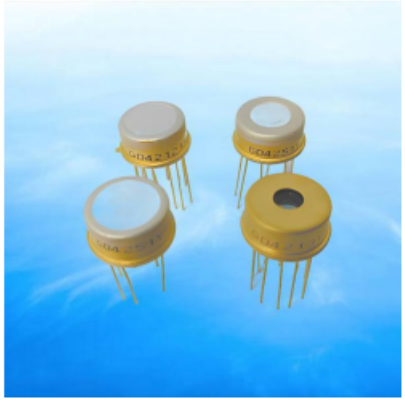
850nmPIN Module series



The device is a silicon PIN photodiode module with a built-in preamplifier circuit, which can amplify the weak current signal and convert it into a voltage signal output, realizing the conversion process of "optical-electrical-signal amplification".

FEATURES

Quick response
High sensitivity

APPLICATION

Laser fuze

Photoelectric characteristics (@Ta＝22±3℃)

Model		GD4213Y	GD4251Y	GD4251Y-A	GD42121Y
Package form		TO-8	TO-8	TO-8	TO-8
Photosensitive surface size (mm)		2	2	10×1.5	10×0.95
Working voltage (V)		±5±0.3	±6±0.3	±6±0.3	±5±0.1
Noise voltage (mV)		12	40	40	25
Responsiveness (M/AY)	λ=850nm,φ=1μW	110	130	130	110
Rise time (ns)		12	12	18	20
Dynamic range (dB) λ=850nm		20	20	20	20
Remark		The light window is plated with a carrier tape filter film (0 degree incidence, 830nm~910nm transmittance ≥ 90%), the test load of GD4213Y is 50Ω, and the test load of other products is 1MΩ.			